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RoHS 2002/95/EC

NTE639
General Purpose Silicon Rectifier
High Voltage, Standard Recovery
DO201AD Type Package

Features:
- Diffused Junction
- Low Forward Voltage Drop
- High Current Capability
- High Reliability
- High Surge Current Capability

Maximum Ratings and Electrical Characteristics:
(T_A = +25°C unless otherwise specified. Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%)

Maximum Peak Repetitive Reverse Voltage, V_{RRM} 1300V
Maximum Working Peak Reverse Voltage, V_{RWM} 1300V
Maximum DC Blocking Voltage, V_R 1300V
Maximum RMS Reverse Voltage, $V_{R(RMS)}$ 910V
Maximum Average Rectified Output Current (.375" (9.5mm) Lead Length, T_A = +75°C), I_O 3A
Non–Repetitive Peak Forward Surge Current, I_{FSM}
(8.3ms Single Half Sine–Wave Superimposed on Rated Load) 200A
Maximum Instantaneous Forward Voltage (I_F = 3A), V_{FM} 1.0V
Maximum Peak Reverse Current (V_R = 1300V), I_{RM}
T_A = +25°C . . . . . 5° A
T_A = +100°C . . . . . 100° A
Typical Junction Capacitance (Note 1), C_j 50pF
Operating Junction Temperature Range, T_J . . . . . –65° to +125°C
Storage Temperature Range, T_{stg} . . . . . –65° to +150°C
Typical Thermal Resistance, Junction–to–Ambient, R_{thJA}
(.375" (9.5mm) Lead Length, T_A = +25°C) . . . . . 20°C/W

Note 1. Measured at 1MHz and applied reverse voltage of 4V.